

Transistors based on two-dimensional materials for fut

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Six Decades of Research on 2D Materials: Progress, Dead Ends, and New Horizons. IEEE Journal of the Electron Devices Society, 2022, 10, 443-451.	2.1	4
2	The role of 2-Dimensional materials for electronic devices. Materials Science in Semiconductor Processing, 2022, 143, 106546.	4.0	18
3	Construction and physical properties of low-dimensional structures for nanoscale electronic devices. Physical Chemistry Chemical Physics, 2022, 24, 9082-9117.	2.8	3
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5	2D materials for future heterogeneous electronics. Nature Communications, 2022, 13, 1392.	12.8	174
6	Mechanical, Elastic, and Adhesive Properties of Two-Dimensional Materials: From Straining Techniques to State-of-the-Art Local Probe Measurements. Advanced Materials Interfaces, 2022, 9, .	3.7	24
7	Two-Dimensional Field-Effect Transistor Sensors: The Road toward Commercialization. Chemical Reviews, 2022, 122, 10319-10392.	47.7	89
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